

General Description

The WSK140N06 is the highest performance trench N-Ch MOSFET with extreme high cell density , which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

Product Summery

BV _{DSS}	R _{DSON}	I _D
60V	$5.3 m\Omega$	140A

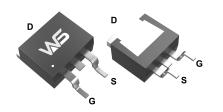
Applications

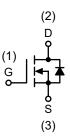
Power Management for Inverter Systems.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

TO-263-2L Pin Configuration





Absolute Maximum Ratings

Symbol	Parameter	Rating	Unit	
VDSS	Drain-Source Voltage		60	V
Vgss	Gate-Source Voltage		±20	V
lo	Continuous Drain Current	Tc=25°C	140	Α
	Continuous Diain Current	Tc=100°C	70	Α
IDM	Pulsed Drain Current *	Tc=25°C	380	Α
Pb	Maximum Power Dissipation	Tc=25°C	107	W
		Tc=100°C	53	W
Is	Diode Continuous Forward Current	Tc=25°C	140	Α
Eas	Avalanche Energy, Single Pulsed	L=1mH	500	mJ
TJ	Maximum Junction Temperature		150	°C
Тѕтс	Storage Temperature Range		-55 to 150	°C

Thermal Resistance

Symbol	Parameter	Rating	Unit
ReJC	Thermal Resistance-Junction to Case	1.4	°C/W
ReJA	Thermal Resistance-Junction to Ambient	62	C/VV

Note:

- * Repetitive rating ; pulse width limited by junction temperatu
- ** Drain current is limited by junction temperature



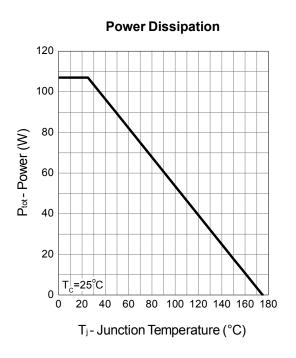
Electrical Characteristics (T= 25 °C Unless Otherwise Noted)

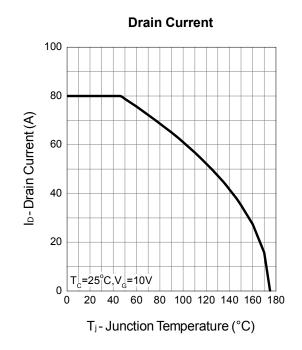
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit	
Static Characteristics							
BVDSS	Drain-Source Breakdown Voltage	Vgs=0V, Ips=250uA	60	-	-	٧	
Ipss	Zero Gate Voltage Drain Current	V _{DS} =60V, V _{GS} =0V	-	-	1	- uA	
IDSS		TJ=85°C	-	-	10		
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250uA	2.0	3.0	4.0	٧	
Igss	Gate Leakage Current	V _G s=±20V, V _D s=0V	-	-	±100	nA	
RDS(ON)*	Drain-Source On-state Resistance	Vgs=10V, Ips=40A	-	5.3	7.0	mΩ	
Diode Chara	ncteristics						
V _{SD*}	Diode Forward Voltage	Isp=20 A, Vgs=0V	-	-	1.3	٧	
trr	Reverse Recovery Time	Isp=40A, disp/dt=100A/us	-	45	-	ns	
Qrr	Reverse Recovery Charge	ISD-40A, disb/dt-100A/dS	-	65	-	nC	
Dynamic Characteristics							
Rg	Gate Resistance	V _G s=0V,V _D s=0V,F=1MHz	-	1.1	-	Ω	
Ciss	Input Capacitance		-	4136	-		
Coss	Output Capacitance	V _{GS} =0V, V _{DS} =25V, Frequency=1.0MHz	-	340	-	pF	
Crss	Reverse Transfer Capacitance		-	260	-		
td(ON)	Turn-on Delay Time		-	22	-		
Tr	Turn-on Rise Time	V _{DD} =30V, R _G =1.8 Ω, I _{DS}	-	24	-	ns	
td(OFF)	Turn-off Delay Time	=1A, V gs=10V,	-	108	-		
Tf	Turn-off Fall Time		-	50	-		
Gate Charge	Characteristics			-	•		
Qg	Total Gate Charge		-	90	-		
Qgs	Gate-Source Charge	V _{DS} =30V, V _{GS} =10V, I _{DS} =40A	-	15	-	nC	
Qgd	Gate-Drain Charge		-	28	-		

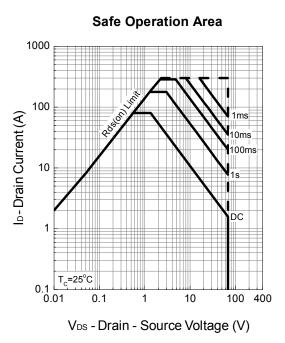
Note * : Pulse test ; pulse width≤300us, duty cycle≤2%.

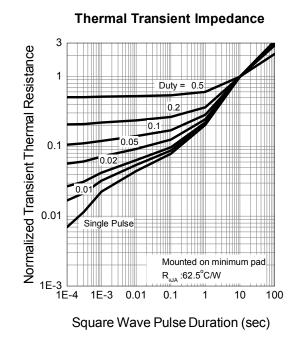


Typical Operating Characteristics



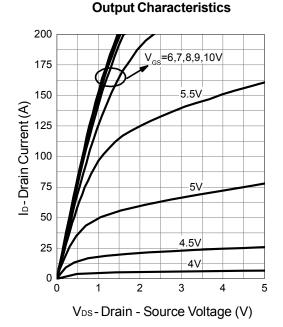




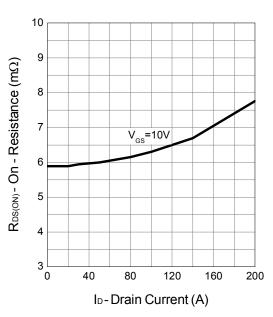




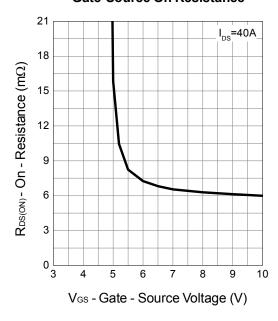
Typical Operating Characteristics (Cont.)



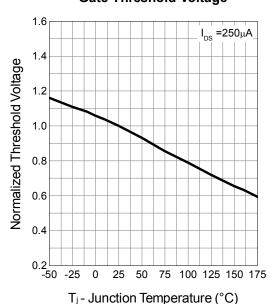
Drain-Source On Resistance



Gate-Source On Resistance

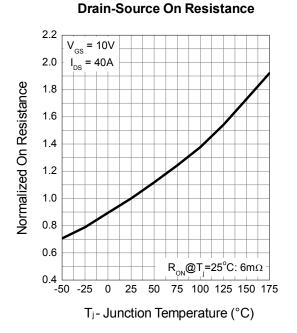


Gate Threshold Voltage

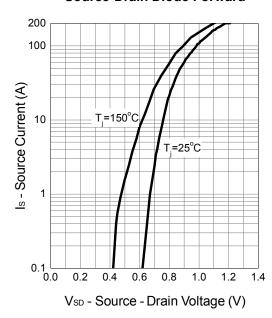




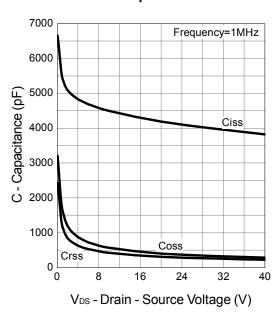
Typical Operating Characteristics (Cont.)



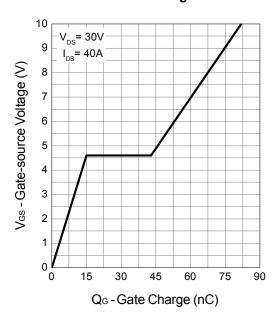
Source-Drain Diode Forward



Capacitance

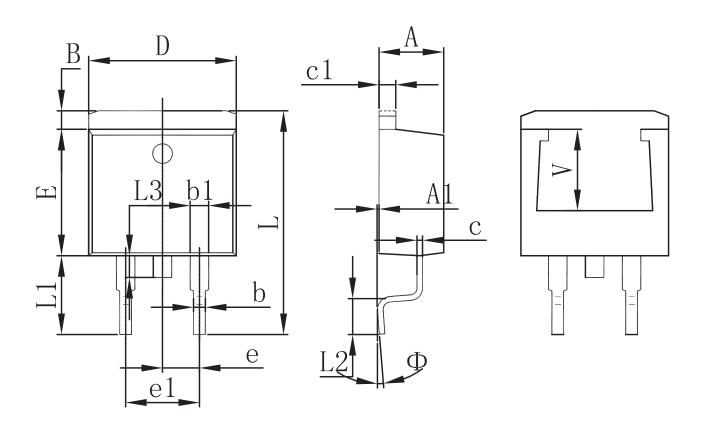


Gate Charge





Packaging information



Cymbol	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
Α	4.470	4.670	0.176	0.184	
A1	0.000	0.150	0.000	0.006	
В	1.120	1.420	0.044	0.056	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.310	0.530	0.012	0.021	
c1	1.170	1.370	0.046	0.054	
D	10.010	10.310	0.394	0.406	
Е	8.500	8.900	0.335	0.350	
е	2.540 TYP.		0.100 TYP.		
e1	4.980	5.180	0.196	0.204	
L	14.940	15.500	0.588	0.610	
L1	4.950	5.450	0.195	0.215	
L2	2.340	2.740	0.092	0.108	
L3	1.300	1.700	0.051	0.067	
Ф	0°	8°	0°	8°	
V	5.600 REF.		0.220REF.		



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